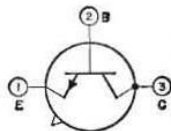


TRANSISTOR



Silicon n-p-n type used in very-high-speed switching and high-frequency applications in equipment which requires high reliability and high packaging densities. JEDEC No. TO-18 package; outline 12, Outlines Section.

2N708

MAXIMUM RATINGS

Collector-to-Base Voltage (with emitter open)	40 max	vols
Collector-to-Emitter Voltage:		
With external base-to-emitter resistance = 10 ohms or less ..	20 max	vols
With base open	15 max	vols
Emitter-to-Base Voltage (with collector open)	5 max	vols
Transistor Dissipation:		
At case temperatures up to 25°C	1.2 max	watts
At ambient temperatures up to 25°C	0.36 max	watt
At case or ambient temperatures above 25°C	See curve page 80	
Temperature Range:		
Operating (junction)	-65 to 200	°C
Storage	-65 to 300	°C
Lead Temperature (for 10 seconds maximum)	300 max	°C

CHARACTERISTICS

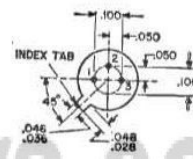
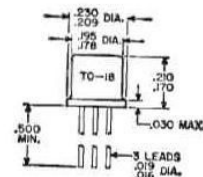
Base-to-Emitter Saturation Voltage		
(with collector ma = 10 and base ma = 1)	0.8 max	volt
Collector-to-Emitter Saturation Voltage		
(with collector ma = 10 and base ma = 1)	0.4 max	volt
Collector-Cutoff Current (with collector-to-base volts = 20		
and emitter ma = 0)	0.025 max	µa

In Common-Base Circuit

Collector-to-Base Capacitance (with collector-to-base volts = 10		
and emitter current = 0)	6 max	pf

In Common-Emitter Circuit

Small-Signal Forward Current-Transfer Ratio (with collector-		
to-emitter volts = 10, collector ma = 10, and frequency		
= 100 Mc)	3 min	
DC Forward Current-Transfer Ratio:		
With collector-to-emitter volts = 1 and collector ma = 10	30 to 120	
With collector-to-emitter volts = 1 and collector ma = 0.5	15 min	



- 12 -